



DOCKET NO. 241189US2S/sm

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Wataru SAITO, et al.

SERIAL NUMBER: 10/634,917

GROUP: 2822

FILED: August 6, 2003

EXAMINER: LEWIS, MONICA

FOR: A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY USED FOR POWER CONTROL

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE
COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: **A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY USED FOR POWER CONTROL.**

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Marvin J. Spivak
Registration No. 24,913

Joseph Scafetta, Jr.
Registration No. 26,803

Customer Number

22850

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/04)